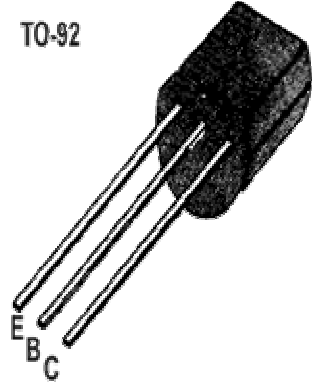


■ ■ APPLICATION: High Frequency Low Noise Amplifier Application.
HF, VHF Band Amplifier Application.

■ ■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V _{EBO}	4	V
Collector current	I _C	25	mA
Collector Power Dissipation	P _C	400	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■ ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	28		198		V _{CE} = 5 V, I _C = 1 mA
Collector Cut-off Current	I _{CBO}			0.1	μA	V _{CB} =30 V, I _E =0
Emitter Cut-off Current	I _{EBO}			0.1	μA	V _{EB} = 3 V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	30			V	I _C =0.1 mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	20			V	I _C =1 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	4			V	I _E = 0.1mA, I _C =0
Base-Emitter Voltage	V _{BE}		0.72		V	V _{CE} =5 V, I _C = 1mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.3	V	I _C =10 mA, I _B =1 mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			1.0	V	I _C = 10mA, I _B =1 mA
Gain bandwidth product	f _T	400			MHz	I _C = 1 mA, V _{CE} =5 V
Common Base Output Capacitance	C _{ob}		1.2	1.6	PF	V _{CB} = 10V, I _E =0, f= 1 MHz
Noise Figure	N _F		3.0	5.0	dB	V _{CE} = 5 V, I _C = 1 mA, f=100 MHz, R _g = 50Ω

■ ■ h_{FE} Classification And Marking

Classification	D	E	F	G	H	I
h _{FE}	28~45	39~60	54~80	72~108	97~146	132~198